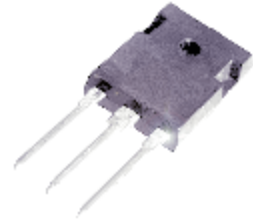




N Channel Lateral Mosfet

- Designed specifically for linear audio amplifier applications
- High-speed for high bandwidth amplifiers
- High voltage rating - 160V
- TO-247 plastic package
- Enhanced oscillation suppression in multi-device applications
- Complementary P-channel available – ECX08P16-Z



ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C unless otherwise stated)

V _{DSS}	Drain – Source Voltage	160V
V _{GSS}	Gate – Source Voltage	+/- 20V
I _D	Continuous Drain Current	8A
I _{DR}	Body Drain Diode Current	8A
P _D	Allowable Power Dissipation* T _{case} = 25°C	125W
T _{ch}	Channel Temperature	150°C
T _{stg}	Storage Temperature Range	-55 to +150°C

*Thermal Resistance, Junction To Case

1.0 deg/watt

WARNING: These lateral mosfets do not include a G-S protection network and care must therefore be taken with static handling precautions and the appropriate protection in the amplifier circuit.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
BV_{DSX}	Drain-Source Breakdown Voltage	$V_{GS} = 10V$ $I_D = 10mA$	160			V
I_{GSS}	Gate-Source Leakage Current	$V_{DS} = 0$ $V_{GS} = \pm 20V$			100	μA
$V_{GS(off)}$	Gate-Source Cut-off Voltage	$V_{DS} = -10V$ $I_D = 100mA$	0.15		1.5	V
$V_{DS(sat)}^*$	Drain-Source Saturation Voltage	$V_{GD} = 0$ $I_D = 16A$			12	V
$ y_{fs} ^*$	Forward Transfer Admittance	$V_{DS} = 10V$ $I_{DS} = 3A$	0.7		2	S(Ω)
I_{DSX}	Drain-Source Cut-Off Current	$V_{GS} = 10V$ $V_{DS} = 200V$			10	mA

* Pulse Test: Pulse Width = $300\mu s$, Duty Cycle $\leq 2\%$

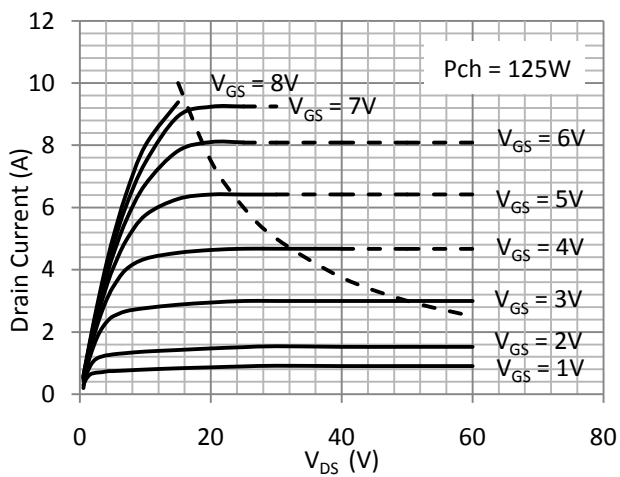
DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{GS} = 0$		500		pF
C_{oss}	Output Capacitance	$V_{DS} = 10V$		300		
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$		10		
t_{on}	Turn-On Time	$V_{DS} = 20V$		100		ns
t_{off}	Turn-Off Time	$I_D = 7A$		50		

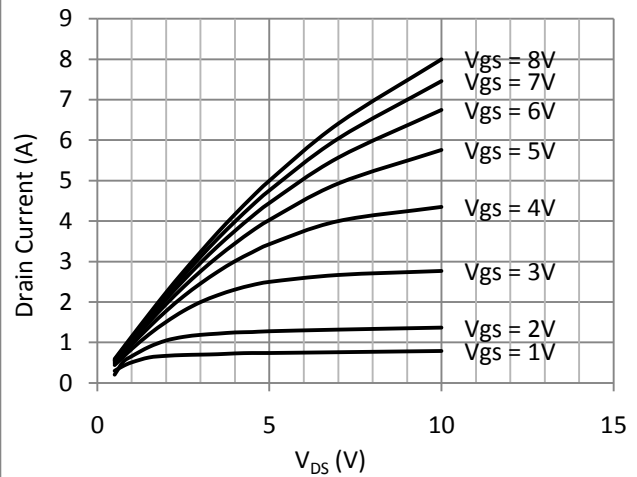


GENERAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

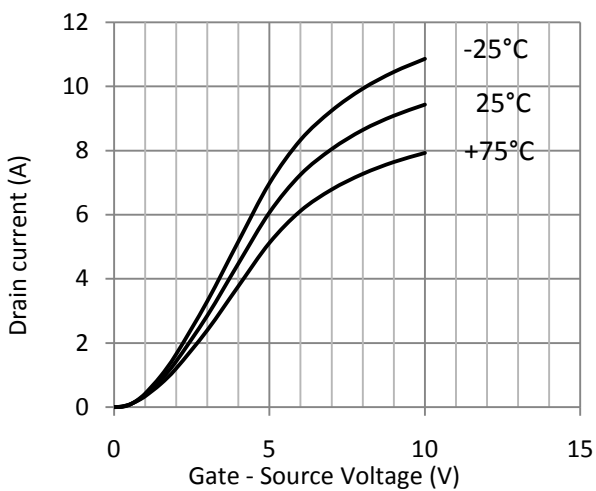
Typical Output Characteristics



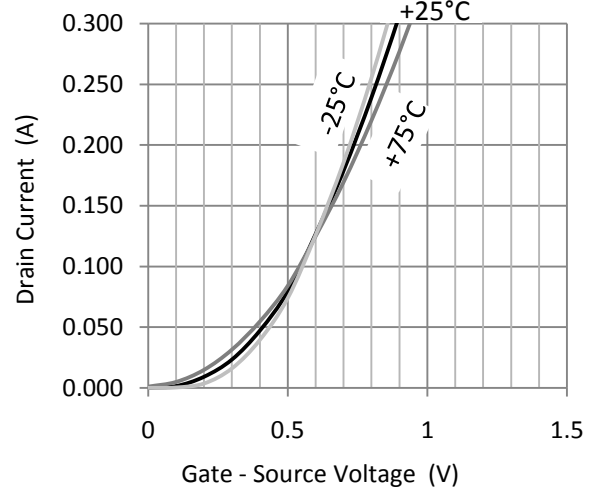
Typical Output Characteristics



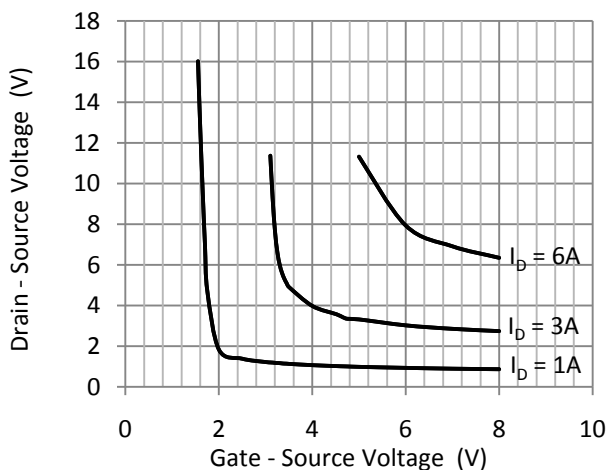
Transfer Characteristic



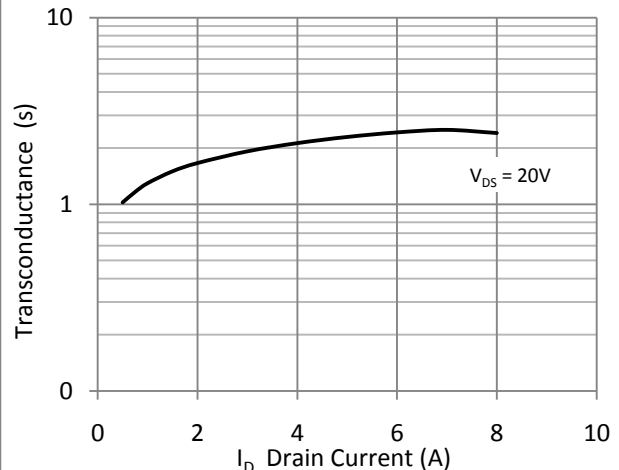
Transfer Characteristic



Drain - Source Voltage vs Gate - Source Voltage

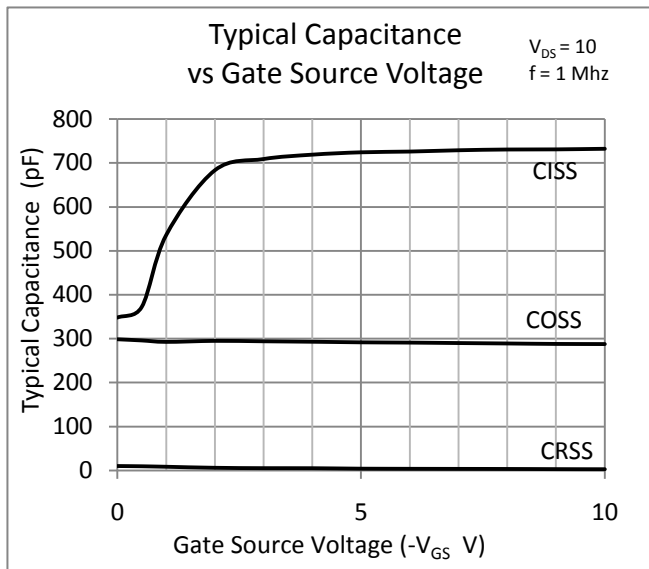
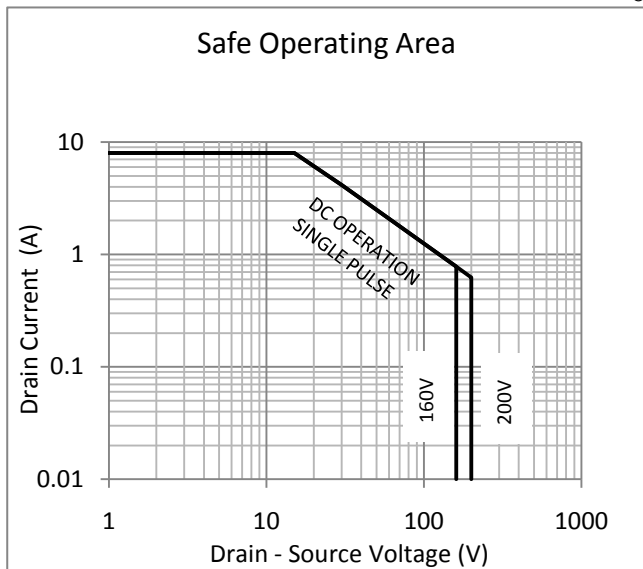


Transconductance



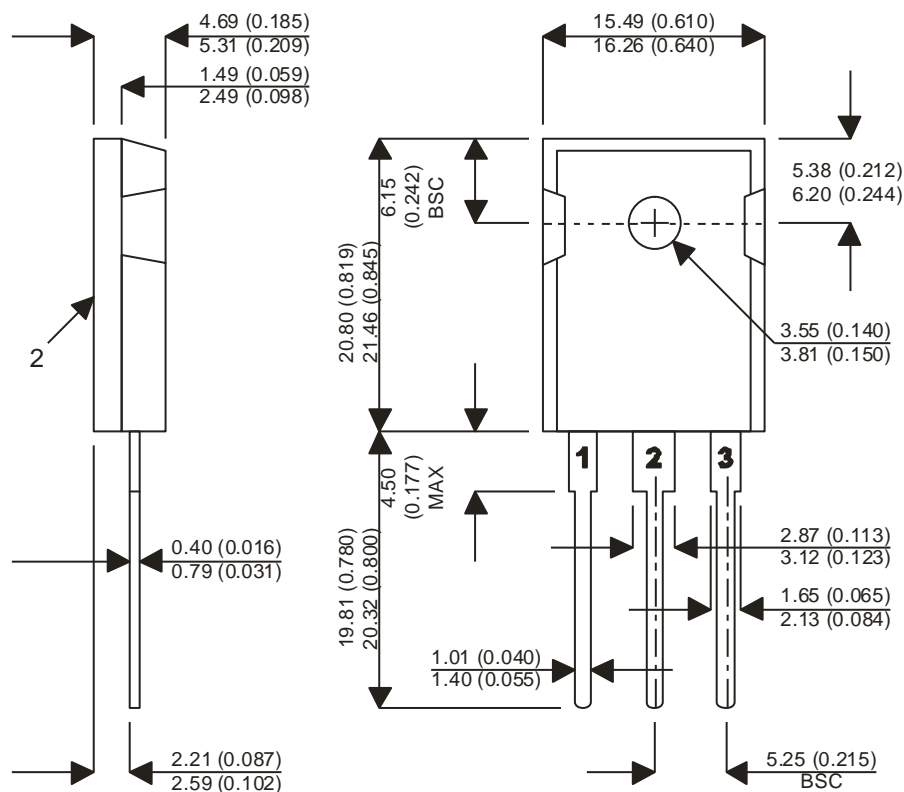


GENERAL CHARACTERISTICS CONTINUED ($T_C = 25^\circ\text{C}$ unless otherwise stated)



MECHANICAL DATA

Dimensions in mm (Inches)



TO-247

Pin 1 - Gate Pin 2 -Source Pin 3 - Drain

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